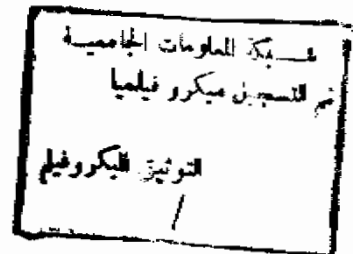

AIN SHAMS UNIVERSITY
FACULTY OF ENGINEERING
Electronics & Electrical Comm. Eng. Dept.

رسالة

MODULATION OF OPTICAL BEAM
IN SEMICONDUCTOR LASER

BY

Eng. / Fadia Aly Ahmed



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A Thesis

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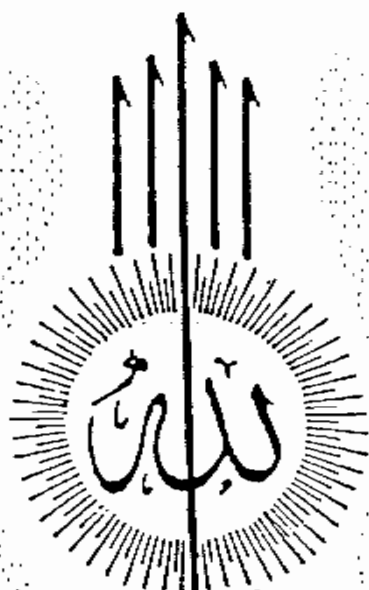
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requirements of the degree of M.Sc.
in electrical engineering.

Supervised By



Prof. Dr. / Magdy Mahmoud Ibrahim
Prof. Dr. / Mahmoud Hanafy Ahmed

CAIRO 1994



بِسْمِ اللَّهِ الرَّحْمَنِ الرَّحِيمِ

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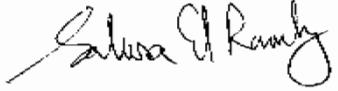
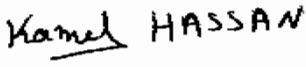
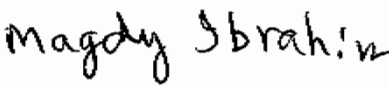
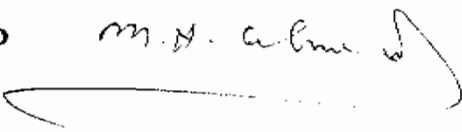
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EXAMINERS COMMITTEE

<u>NAME , TITLE AND AFFILIATION</u>	<u>SIGNATURE</u>
1- PROFESSOR \ SALWA HUSSEIN ELRAMLY	
2- PROFESSOR \ KAMEL MOHAMED HASAN	
3- PROFESSOR \ MAGDY MAHMOUD IBRAHIM	
4- PROFESSOR \ MAHMOUD HANAFY AHMED	

AIN SHAMS UNIVERSITY
FACULTY OF ENGINEERING

(C . V .)

* Student Name : *Fadia Aly Ahmed.*

* Date of Birth : *23-12-1960.*

* Place of Birth : *Cairo.*

* First University Degree :

*B.Sc. Electrical Engineering, Electronics and
Communications Department, Ain Shams University,
June 1984.*

* Previous Experience :

*Optical Communication and Lasers Lab. Engineer, Faculty
of Engineering, Ain Shams University, 1986-1994.*

* Present Job :

*Optical Communication and Lasers Lab. Engineer, Faculty
of Engineering, Ain Shams University.*

Name : *Fadia Aly Ahmed .*

Signature : *Fadia Aly*

Date :

Statement

This dissertation is submitted to Ain Shams University for the degree of M.Sc. in Electrical Engineering.

The work included in this thesis was carried out by the auther in the department of Electronics and Communication Engineering, Ain Shams University.

No part of this thesis has been submitted for a degree or a qualification at any other university or institution.

Name : *Fadia Aly Ahmed.*

Signature : *Fadia Aly*

Date :

ABSTRACT

Direct modulation of semiconductor lasers is of a great importance for optical fiber communication systems. A detailed analysis is presented for the modulation performance of an inhomogeneously - pumped s.c. laser using the rate - equations model. This laser is composed of two sections, one for gain, the other acts as an absorber, and they are coupled optically but isolated electrically. It has many applications in optical switching.

The laser threshold current may be reduced by reducing the absorber length, or by increasing its pumping current. The stability analysis of the laser identifies the pulsation and cw operation region. For a shorter absorber length the stable region extends to a lower value of the absorber pumping current. Increasing the absorber pumping current results in an increase in both the modulation bandwidth and the optical output power.

The gain compression reduces the peak height of the modulation response by about 10 dB in a good agreement with the previous results for a homogeneously pumped s.c. laser.

An inhomogeneously pumped s.c. laser has a better modulation response than a homogeneously pumped laser, when a suitable pumping current is applied to the absorber section.

Negative electronic feedback reduces the output power and has a weak effect on the modulation response, but it increases the dynamic stable region.

List of Symbols

A_i	Loop gain .
A_2	Proportionality spontaneous constant .
B	Phase constant .
B_{12}	Absorption proportionality constant .
B_{21}	Stimulated proportionality constant .
c	Velocity of light .
E	Energy level .
E_c	Conduction band energy .
E_v	Valence band energy .
E_g	Gap energy .
E_f	Fermi level energy .
E_{ph}	Photon energy .
$F(\epsilon)$	Fermi function .
f_c	Occupation probability for electrons in the conduction band .
f_v	Occupation probability for holes in the valence band .
f_o	Relaxation oscillation frequency .
G_o	Linear gain .
g	Cavity gain .
h	Planck's constant .
I	Injection current .
I_f	Feedback current .
I_{th}	Threshold current .
J_n	Injected electrons .
J_p	Injected holes .
k	Feedback parameter .
L	Cavity length .
L_{abs}	Absorber length .
m_e	Effective mass of electrons .

m_h	Effective mass of holes .
M_p	Height of the resonance peak .
n	Carrier density .
n'	Real part of refractive index .
n''	Imaginary part of refractive index .
n_0	Carrier density at the transparency .
n_i	Intrinsic carrier concentration .
n_{th}	Carrier density at threshold .
n_{sp}	Spontaneous emission rate .
n_1	Carrier density for gain section .
n_2	Carrier density for absorber section .
n_{o1}	Carrier transparency of gain section .
n_{o2}	Carrier transparency of absorber section .
P	Concentration of holes .
P_o	Optical power .
r_1	Fraction volume of gain section .
r_2	Fraction volume of absorber section .
r_{12}	Absorption rate .
r_{21}	Rate stimulated emission .
r_s	Beam splitter reflectivity.
r_{sp}	Spontaneous emission rate .
R	Mirror reflectivity .
R_p	Responsivity of a photo-diode .
s	Photon density .
T	Absolute temperature .
T_o	Characteristic temperature .
V	Active region volume .
v_g	Group velocity .
α'	Linewidth enhancement factor .
α_m	Cavity mirror loss .
α_s	Cavity loss .
β	Differential loss coefficient .
ϵ	Gain compression coefficient .

γ_d	Damping factor .
η_i	Internal quantum efficiency .
μ	Refractive index .
τ_e	Carrier life time of gain section .
τ_t	Carrier life time of absorber section .
τ_i	Intra-band relaxation time .
τ_{ph}	Photon life time .
ω_o	Oscillation frequency .
ω_d	Damping frequency .
ω_P	Frequency of resonance peak .
ω_{-3dB}	-3dB frequency .
ρ	Electron state density .
λ	Emission wave length .
Γ	Confinement factor .
ν	Frequency of optical wave .
Δ_D	Dip in the modulation response .

CONTENTS

INTRODUCTION	1
CHAPTER 1. SEMICONDUCTOR LASERS	4
1-1 INTRODUCTION	4
1-2 Semiconductor Material Properties	7
1-2-1 P-Type & N-Type Semiconductors	7
1-2-2 High Doping Effect	8
1-3 Direct and Indirect Semiconductors	9
1-4 P-N Junction	9
1-4-1 Unbiased P-N Junction	9
1-4-2 Biased P-N Junction	12
1-5 The Use of Heterostructure	12
1-5-1 Heterojunctions	12
1-5-2 Double Heterostructure characteristics...	14
1-6 Mechanisms of Radiation Transitions	14
1-6-1 Spontaneous Emission	17
1-6-2 Stimulated Emission and Absorption	18
1-6-3 Gain Calculation	18
1-7 Semiconductor Laser characteristics	19
1-7-1 Lasing Conditions	19
1-7-2 Dynamic Characteristics of Laser Operation	21
1-7-3 Light current Characteristics of Laser Operation	22
1-7-4 Basic Laser Structure	23
1-8 Laser Spectral Characteristics	25
1-8-1 Spectral Hole Burning	25
1-8-2 Non Linear Gain	25
1-8-3 Laser Linewidth	28

CHAPTER 2	MODULATION OF SEMICONDUCTOR LASERS	30
2-1	INTRODUCTION	30
2-2	Intensity Modulation	32
2-2-1	Rate Equations	32
2-2-2	Threshold current	33
2-2-3	Steady State Characteristics	33
2-2-4	Small Signal Response	34
2-3	Relaxation Oscillation Frequency	35
2-4	Parameters Affecting the Resonance Frequency (f_0)	35
2-4-1	The Differential Gain Constant (α)	36
2-4-2	The Photon Density (S)	37
2-4-3	The Photon Life Time	40
2-5	Damping Frequency	40
2-6	Effects that Influences the Intensity Modulation Response	42
2-6-1	The Bias Current	42
2-6-2	Electrical Parasitics	45
2-6-3	Lateral Diffusion	47
2-6-4	Longitudinal Mode Spectrum	49
2-6-5	High Doping Effect	51
2-6-6	The Laser Structure	53
2-7	High Speed Limitations	53
2-8	Intensity Noise	57
2-8-1	Relative Intensity Noise RIN	58
2-9	Further Bandwidth Enhancement	58
2-9-1	InGaAsP/InP DFB Laser with an Air-Bridge Contact	60
2-9-2	InGaAs/InP Buried Straight-Wall Mass Transport BH Laser Diode MTBH	62
2-9-3	InGaAsP Semi-Insulating Buried Crescent Lasers	62
2-10	External Modulation	66

2-10-1	Modulator Devices Using Absorption Gain Change	67
2-10-2	Modulators Devices Using Refractive Index Change	67
2-10-3	Monolithic Integration Devices	67

CHAPTER	3	MODULATION OF INHOMOGENEOUSLY PUMPED SEMICONDUCTOR LASER.	71
3-1		Introduction	71
3-2		The Description Of Inhomogeneously Pumped Semiconductor Laser	73
3-3		The Importance of the Inhomogeneously Pumped Semiconductor Laser Device In High Speed Communication Application ...	73
3-3-1		An Optical Stylus	74
3-3-2		Optical Set-Reset Pulses	75
3-3-3		Mode Locking a Semiconductor Laser at Frequencies Beyond 100 GHz	75
3-3-4		Optical AND Logic and OR Logic	77
3-3-5		The Generation of a Picosecond High Power Pulse	79
3-3-6		A Narrow Bandwidth High Gain Optical Filter	79
3-3-7		Photonic Memory Switch	79
3-4		Basic Rate Equations	81
3-5		Steady State Characteristics	84
3-6		The Threshold Condition	90
3-7		Stability Analysis	93
3-7-1		Small Signal Analysis	94
3-7-2		Stability Conditions	95
3-8		Frequency Response	97
3-8-1		Effect of Absorber Pumping Current on Both	

	Modulation Response and Generated Optical Power	99
3-8-2	Effect of Absorber Length on the Modulation Response	102
3-8-3	The Effect of Gain Compression on Modulation Response of Inhomogeneously Pumped Laser	106
3-8-4	Comparison Between Homogeneously and Inhomogeneously Pumped Semiconductor Laser w.r.t Modulation Response and Generated Optical Power	109

CHAPTER 4

	THE EFFECT OF ELECTRONIC FEEDBACK (EFB) ON INHOMOGENEOUSLY PUMPED SEMICONDUCTOR LASER	115
4-1	Introduction	115
4-2	Model of the inhomogeneously pumped S.C. with EFB.....	116
4-3	Static and Dynamic Characteristics of Inhomogeneously Pumped Laser with Negative EFB Applied on its Gain Section	120
4-3-1	Steady State Characteristics with Negative EFB Applied on The Gain Section	121
4-3-2	The Effect of Negative EFB Applied on The Gain Section on The Stability of Inhomogeneously Pumped Laser	121
4-3-3	Effect of Negative EFB Applied on the Gain Section on the modulation Response of Inhomogeneously Pumped Laser	122
4-4	The Effect of Negative EFB Applied on Absorber Section of the Inhomogeneously Pumped Semiconductor Laser	124